

Silicon NPN Power Transistors

MJW21192

DESCRIPTION

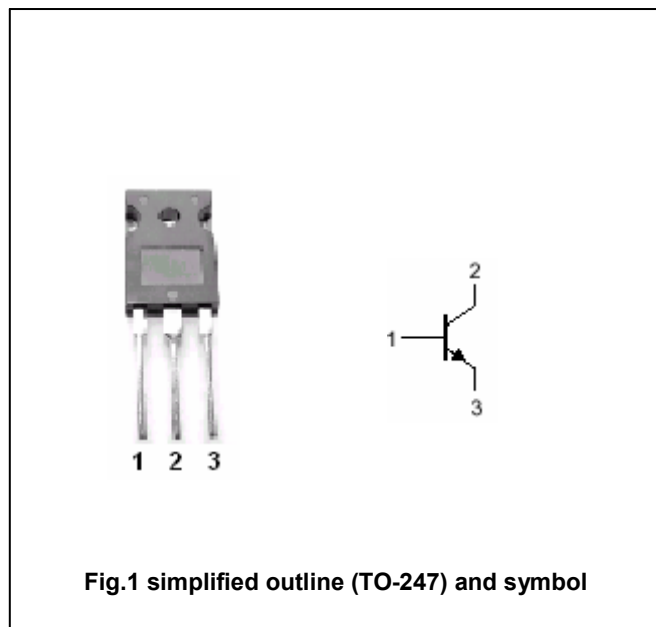
- With TO-247 package
- Complement to type MJW21191
- Wide area of safe operation

APPLICATIONS

- Designed for power audio output, high power drivers in audio amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

ABSOLUTE MAXIMUM RATINGS($T_C=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	150	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak		16	A
I_B	Base current		2	A
P_D	Total power dissipation	$T_C=25^{\circ}\text{C}$	100	W
T_j	Junction temperature		-65~150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-65~150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-C}$	Thermal resistance from junction to case	0.65	$^{\circ}\text{C}/\text{W}$

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CHARACTERISTICS

T_j=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =10mA ; I _B =0	150			V
V _{CE(sat)-1}	Collector-emitter saturation voltage	I _C =4A; I _B =0.4A			1.0	V
V _{CE(sat)-2}	Collector-emitter saturation voltage	I _C =8A; I _B =1.6A			2.0	V
V _{BE(ON)}	Base-emitter on voltage	I _C =4A ; V _{CE} =2V			2.0	V
I _{CES}	Collector cut-off current	V _{CB} =150V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =4A ; V _{CE} =2V	15		100	
h _{FE-2}	DC current gain	I _C =8A ; V _{CE} =2V	5			
f _T	Transition frequency	I _C =1.0A ; V _{CE} =10V, f=1MHz	4.0			MHz

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PACKAGE OUTLINE

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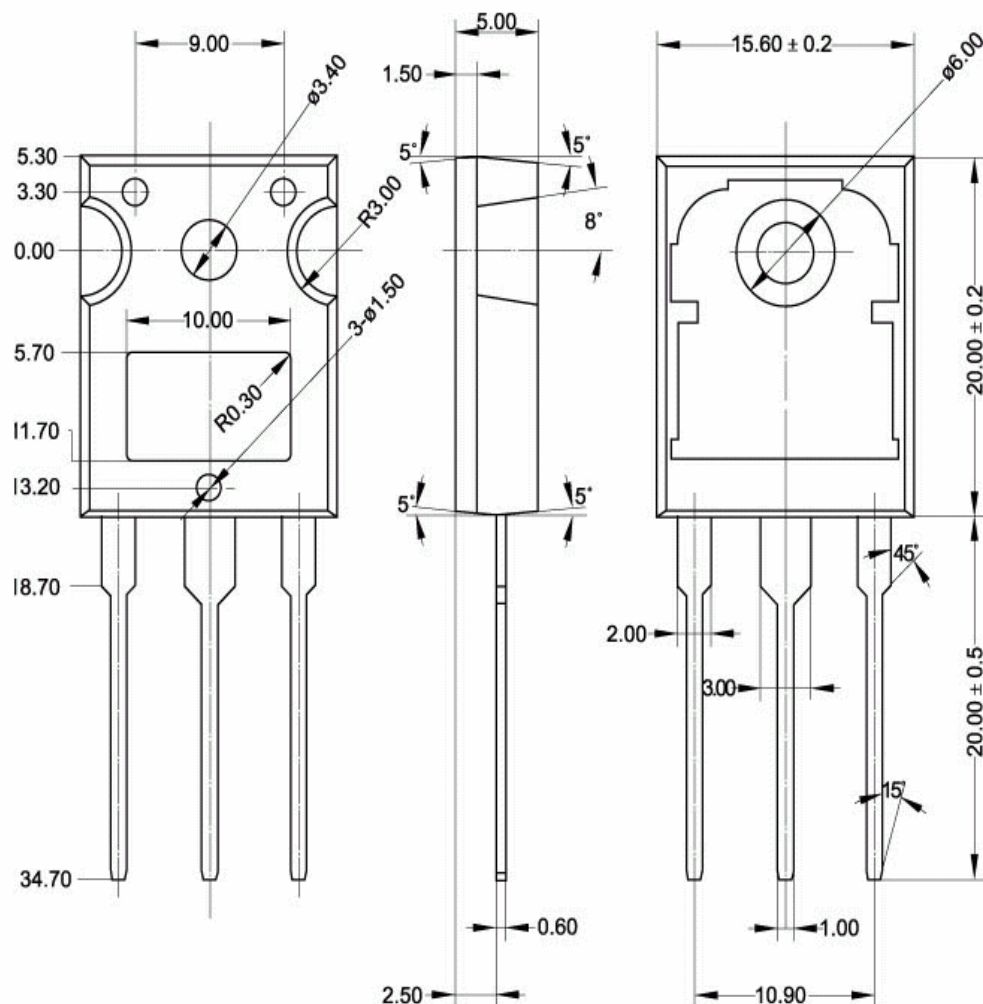


Fig.2 Outline dimensions